

• Supplementary File •

## Investigation of NbO<sub>x</sub>-based volatile switching device with self-rectifying characteristics

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### Appendix A Supplementary figure

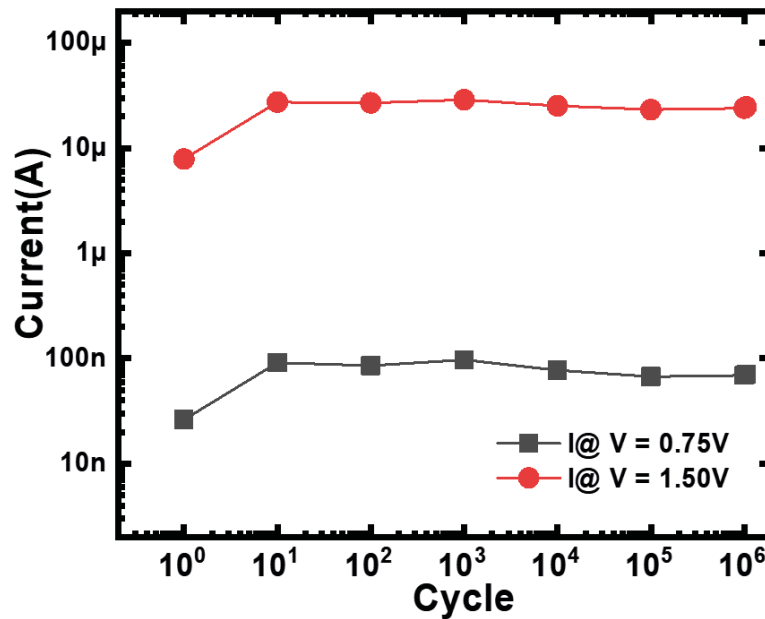


Figure A1 The endurance of the niobium-oxide based device is larger than 10<sup>6</sup>

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